

March 6-9, 2011 Nagoya Institute of Technology, Nagoya, Japan

Chairperson: Masaru Hori, Plasma Nanotechnology Research Center, Nagoya University

Vice-Chairperson: Hideki Masuda, Nagoya Institute of Technology

Hiroshi Amano, Nagoya University Keiji Nakamura, Chubu University

ISPlasma2011 is specialized international symposium where world-leading researchers can gather in the Tokai region to discuss not only advanced plasma science, its application for nitrides, and nanomaterials, but also new systems for industrial technological transfers. By holding this symposium, where the latest research can be presented and discussed, we aim at two goals. First, we aim to establish an advanced plasma science and technology center in this region that can collaborate with research institutes worldwide. Our second goal is to address issues such as global warming and resources and energy problems where advanced plasma science and its application technology can serve. We aspire to contribute to the evolution of environmental, energy science and technology.

RELATED FIELDS

- Plasma Science and Technology Advanced Plasma & Surface Diagnostics/Simulation and Database/Etching Process/ Deposition Process/Solar Cells Based on Plasma Science/Advanced Plasma Flexible Electronics
- Nitride Semiconductors Crystal Growth of GaN and Related Materials/MBE Growth of Nitrides/Characterization/Device Processing/Electronic Devices/Optical Devices
- Nanomaterials Nanocarbon Materials/Porous Materials/Lithium-ion Rechargeable Battery Cells/Surface Modification/Surface Functionalization/Composite/Functionally Grade Materials/Nanoparticles
- Integration Technology of Plasma Science, Nitride Semiconductors and Nanomaterials
- Industry -Academia-Government Collaboration

ABSTRACT SUBMISSION

For more information, please visit http://www.isplasma.jp/ Submission Deadline: Monday, November 8, 2010 (11:00 am Japan Time)

Selected papers will be published in a special issue of Jpn. J. Appl. Phys. (JJAP) . Instruction for submitting papers will be informed by the end of December.

Registration

Registration Fee: General Early Registration (before January 31, 2011) JPY 20,000 JPY 3,000 JPY 5,000 JPY 7,000 Late Registration (until February 28, 2011) JPY 25,000 JPY 30,000 On-site Registration (after March 1, 2011) Banquet Fee (on March 8) JPY 5.000 JPY 2,000

Refunds cannot be made at any reason

For those attending only the March 9, PM Session (Industry-Academia-Government Collaboration Lecture and Panel Discussion): Registration Fee is FREE.

Advanced online registration is required.

Plenary Speaker

Hiroyuki Sakaki (Toyota Technological Institute, JAPAN)

Keynote/Knowledge Cluster Speakers (Tentative)

Plasma Science and Technology

J-P. Booth (CNRS, FRANCE) M. J. Goeckner (University of Texas at Dallas, USA) F. Laermer (Robert Bosch GmbH, GERMANY)

Nitride Semiconductors

D. Alquier (Université de Tours, FRANCE) N. Grandjean (EPFL, SWITZERLAND) F. Scholz (Ulm University, GERMANY) E. Yoon (Seoul National University, KOREA) O. Takai (Nagoya University, JAPAN)

B. Daudin (CEA Grenoble, FRANCE)

K. Mizuuchi (Osaka Municipal Technical Research Institute, IAPAN)

Y. Watanabe (Nagoya Institute of Technology, JAPAN)

A. Krost (Otto von Guericke University Magdeburg, GERMANY) D. Ueda (Panasonic Corp., JAPAN)

U. Czarnetzki (Ruhr-University Bochum, GERMANY)

. G. Han (Sungkyunkwan University, KOREA)

T. Egawa (Nagoya Institute of Technology, JAPAN) F. Ponce (Arizona State University, USA) A. Wendt (University of Wisconsin-Madison, USA)

J. Vlcek (University of West Bohemia, CZECH REPUBLIC)

M Oda (ULVAC Inc. JAPAN) A. Yoshino (Asahi Kasei Corp., JAPAN)

D. B. Graves (UC Berkeley, USA)

M. Kondo (AIST, JAPAN)

Nanomaterials

T Arimoto (IST JAPAN)

M. Meyyappan (NASA Ames Research Center, USA) J. Robertson (Cambridge University, UK) H-C. Zhou (Texas A&M University, USA)

Industry-Academia-Government Collaboration Simultaneous Interpretation W Vandervorst (IMEC BELGIUM) and more

Panel Discussion (Tentative)

Application of Advanced Plasma Technology for Nitride Semiconductors II

Succeeding to ISPlasma 2010, the role of plasma science and technology for applications to nitride semiconductors such as; plasma processing for device fabrication and nitrogen radical source for crystal growth and others will be discussed.

< Moderator > Y. Nanishi (Ritsumeikan University, JAPAN/ Seoul National University, KOREA)

C. Mantel (Selantek, Inc., USA)

For the Establishment of an Advanced Plasma Science and Technology Center by Open Innovation Simultaneous Interpretation

After reports by specialists from various fields related to open innovation, the way towards establishing an advanced plasma science and technology center in the Tokai region through open

<Moderator> N. Odake (Nagoya Institute of Technology, JAPAN)

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Aichi Prefecture, Nagoya City, Gifu Prefecture, Nagoya University, Nagoya Institute of Technology, Meijo University, Chubu University, The Japan Society of Applied Physics, The Japan Society of Plasma Science and Nuclear Fusion Research

The Japanese Association for Crystal Growth

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